

L Number	Hits	Search Text	DB	Time stamp
1	337	(257/332).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16 09:36
2	79	((257/332).CCLS.) and breakdown adj voltage	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16 09:36
3	258	((257/332).CCLS.) not (((257/332).CCLS.) and breakdown adj voltage)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16 09:54
5	208	(257/333).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16 10:05
6	254	trench near (MOSFET DMOS) and breakdown adj voltage and epitaxial\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16 10:40
7	46	(trench near (MOSFET DMOS) and breakdown adj voltage and epitaxial\$2) and deep adj body	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16 10:05
8	10	6262453.URPN.	USPAT	2004/07/16 10:17
11	757	(VDMOS trench near (gate MOSFET DMOS)) and breakdown adj voltage and epitaxial\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16 11:01
12	10	((VDMOS trench near (gate MOSFET DMOS)) and breakdown adj voltage and epitaxial\$2) and (field adj relief gaurd adj ring)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16 10:48
13	7	((VDMOS trench near (gate MOSFET DMOS)) and breakdown adj voltage and epitaxial\$2) and buried adj region with body	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16 10:49
14	184	(257/334).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16 10:49
15	424	(257/331).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16 11:07
16	584	(257/339).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16 11:01
18	100	(VDMOS trench near (gate MOSFET DMOS)) and ((257/339).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16 11:01
20	951	(257/330).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16 11:20
25	543	(257/302).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16 11:53
-	1	10/603461	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/13 12:54

-	2	10/437984	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/13 13:09
-	21	US-6090716-\$.DID. OR US-6069043-\$.DID. OR US-5910669-\$.DID. OR US-5674766-\$.DID. OR US-5665996-\$.DID. OR US-5592005-\$.DID. OR US-5298442-\$.DID. OR US-5072266-\$.DID. OR US-5034785-\$.DID. OR US-4967245-\$.DID. OR US-4767722-\$.DID.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/13 13:56
-	13	(timothy near3 henson).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/13 14:06
-	587	(257/329).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/14 15:26
-	376	((257/329).CCLS.) not (((257/331).CCLS.) ((257/330).CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/14 15:27
-	149	((257/329).CCLS.) not (((257/331).CCLS.) ((257/330).CCLS.))) and trench	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/14 15:27
-	4	((257/330).CCLS.) ((257/331).CCLS.) ((257/329).CCLS.) ((257/332).CCLS.) ((257/333).CCLS.)) and field adj relief adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/14 15:29
-	47	trench near (MOSFET DMOS) and breakdown adj voltage and deep adj body	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/14 15:51
-	1	(trench near (MOSFET DMOS) and breakdown adj voltage and deep adj body) not ((trench near (MOSFET DMOS) and breakdown adj voltage and epitaxial\$2) and deep adj body)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/14 15:51
-	2	trench near (MOSFET DMOS) and breakdown adj voltage and buried adj body	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/14 15:51